

Dual P-channel MOSFET

ELM17801GA-S

General description

ELM17801GA-S uses advanced trench technology to provide excellent $R_{ds(on)}$, low gate charge and operation with gate voltages as low as 1.8V and internal ESD protection.

Features

- $V_{ds} = -20V$
- $I_d = -0.6A$ ($V_{gs} = -4.5V$)
- $R_{ds(on)} < 520m\Omega$ ($V_{gs} = -4.5V$)
- $R_{ds(on)} < 700m\Omega$ ($V_{gs} = -2.5V$)
- $R_{ds(on)} < 950m\Omega$ ($V_{gs} = -1.8V$)
- ESD Rating : 2000V HBM

Maximum absolute ratings

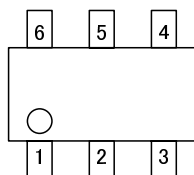
Parameter	Symbol	Limit	Unit	Note
Drain-source voltage	V_{ds}	-20	V	
Gate-source voltage	V_{gs}	± 8	V	
Continuous drain current	I_d	-0.60	A	1
		-0.48		
Pulsed drain current	I_{dm}	-3	A	2
Power dissipation	P_d	0.30	W	1
		0.19		
Junction and storage temperature range	T_j, T_{stg}	-55 to 150	$^{\circ}C$	

Thermal characteristics

Parameter		Symbol	Typ.	Max.	Unit	Note
Maximum junction-to-ambient	$t \leq 10s$	$R\theta_{ja}$	360	415	$^{\circ}C/W$	1
Maximum junction-to-ambient	Steady-state		400	460	$^{\circ}C/W$	
Maximum junction-to-lead	Steady-state	$R\theta_{jl}$	300	350	$^{\circ}C/W$	3

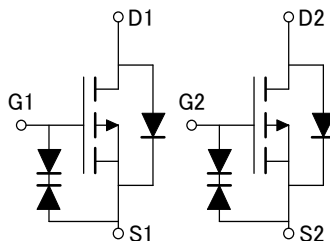
Pin configuration

SC-70-6 (TOP VIEW)



Pin No.	Pin name
1	SOURCE1
2	GATE1
3	DRAIN2
4	SOURCE2
5	GATE2
6	DRAIN1

Circuit



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Electrical characteristics

Ta=25°C

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-source breakdown voltage	BVdss	Id=-250 μA, Vgs=0V	-20			V
Zero gate voltage drain current	Idss	Vds=-16V Vgs=0V			-1	μA
		Tj=55°C			-5	
Gate-source leakage current	Igss	Vds=0V, Vgs=±8V			±10	μA
Gate threshold voltage	Vgs(th)	Vds=Vgs, Id=-250 μA	-0.5	-0.6	-0.9	V
On state drain current	Id(on)	Vgs=-4.5V, Vds=-5V	-3			A
Static drain-source on-resistance	Rds(on)	Vgs=-4.5V		400	520	mΩ
		Id=-0.6A	Tj=125°C	542	700	
		Vgs=-2.5V, Id=-0.5A		540	700	
		Vgs=-1.8V, Id=-0.4A		700	950	mΩ
Forward transconductance	Gfs	Vds=-5V, Id=-0.6A		1.7		S
Diode forward voltage	Vsd	Is=-0.5A, Vgs=0V		-0.86	-1.00	V
Max. body-diode continuous current	Is				-0.4	A
DYNAMIC PARAMETERS						
Input capacitance	Ciss			114	140	pF
Output capacitance	Coss	Vgs=0V, Vds=-10V, f=1MHz		17		pF
Reverse transfer capacitance	Crss			14		pF
Gate resistance	Rg	Vgs=0V, Vds=0V, f=1MHz		12	17	Ω
SWITCHING PARAMETERS						
Total gate charge	Qg	Vgs=-4.5V, Vds=-10V		1.44	1.80	nC
Gate-source charge	Qgs	Id=-0.6A		0.14		nC
Gate-drain charge	Qgd			0.35		nC
Turn-on delay time	td(on)			6.5		ns
Turn-on rise time	tr	Vgs=-4.5V, Vds=-10V		6.5		ns
Turn-off delay time	td(off)	RI=16.7 Ω, Rgen=3 Ω		18.2		ns
Turn-off fall time	tf			5.5		ns
Body diode reverse recovery time	trr	If=-0.6A, di/dt=100A/μs		10	13	ns
Body diode reverse recovery charge	Qrr	If=-0.6A, di/dt=100A/μs		3		nC

NOTE :

1. The value of Rθja is measured with the device mounted on 1in² FR-4 board of 2oz. Copper, in still air environment with Ta=25°C. The value in any given applications depends on the user's specific board design, The current rating is based on the t ≤ 10s thermal resistance rating.
2. Repetitive rating, pulse width limited by junction temperature.
3. The Rθja is the sum of the thermal impedance from junction to lead Rθjl and lead to ambient.
4. The static characteristics in Figures 1 to 6 are obtained using 80μs pulses, duty cycle 0.5%max.
5. These tests are performed with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with Ta=25°C. The SOA curve provides a single pulse rating.

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Typical electrical and thermal characteristics

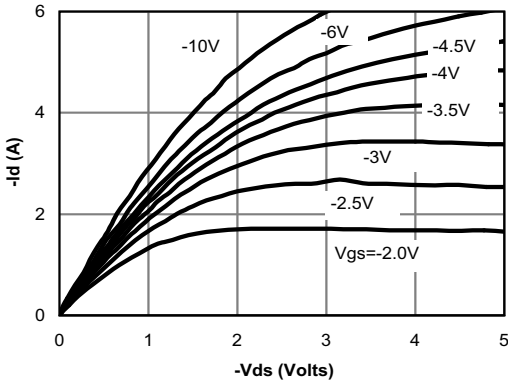


Fig 1: On-Region Characteristics

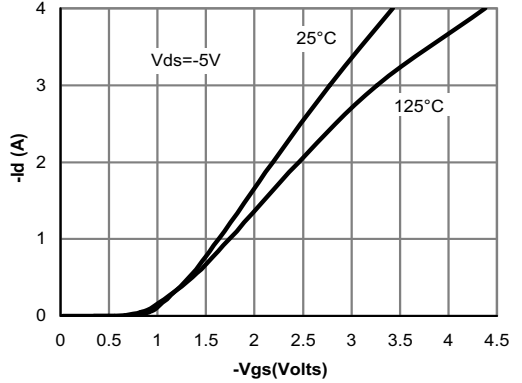


Figure 2: Transfer Characteristics

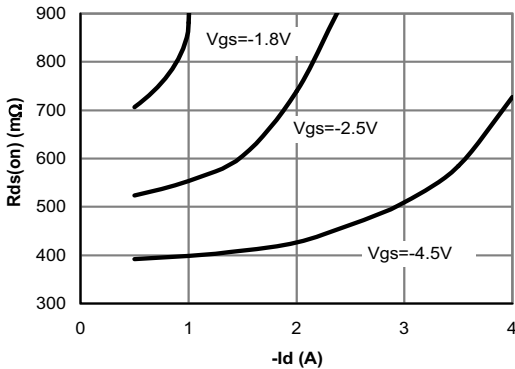


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

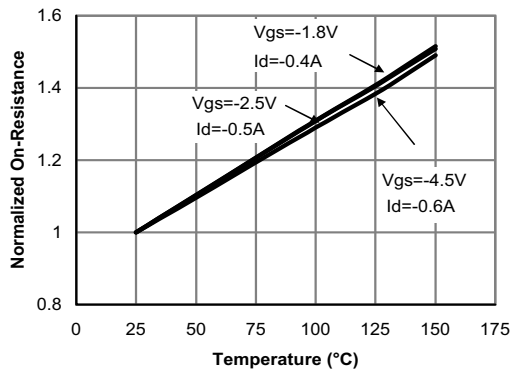


Figure 4: On-Resistance vs. Junction Temperature

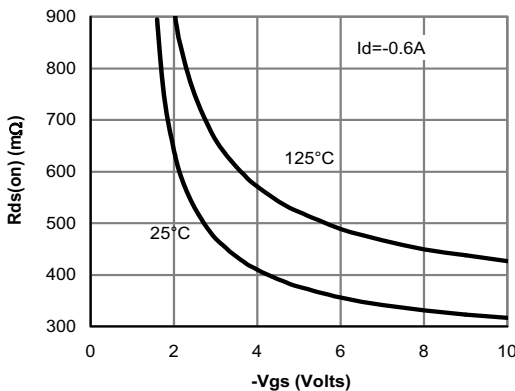


Figure 5: On-Resistance vs. Gate-Source Voltage

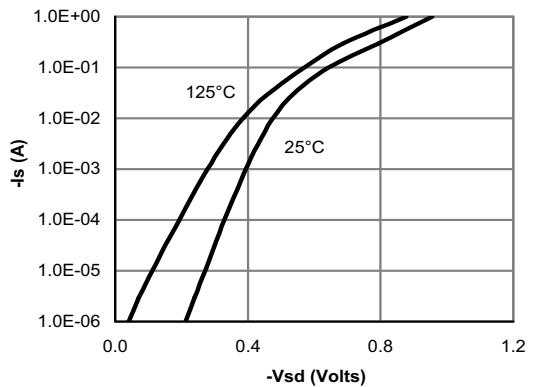


Figure 6: Body-Diode Characteristics

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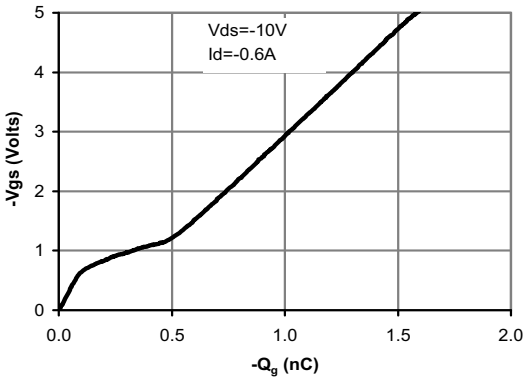


Figure 7: Gate-Charge Characteristics

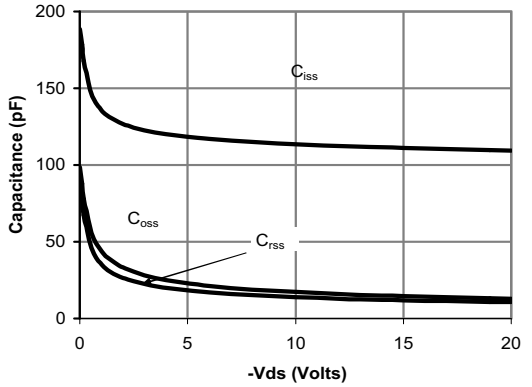


Figure 8: Capacitance Characteristics

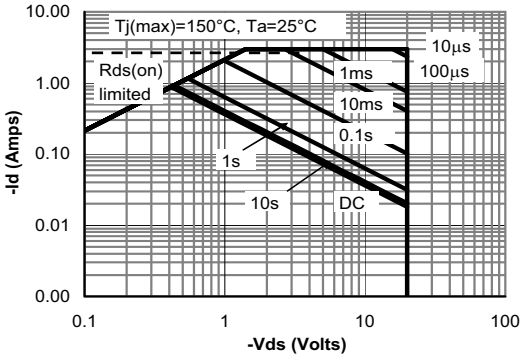


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

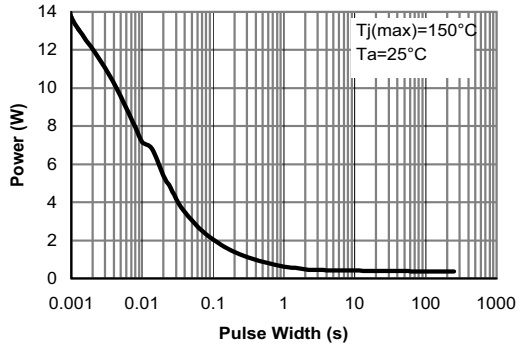


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

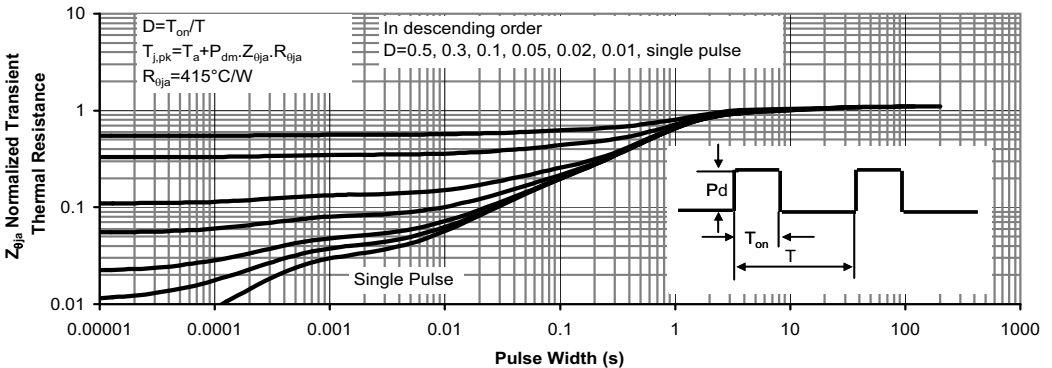


Figure 11: Normalized Maximum Transient Thermal Impedance